

Qinglong Yan

List of Publications by Year in descending order

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Version: 2024-02-01

6
papers

374
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1478505

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1872680

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g-index

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docs citations

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times ranked

264
citing authors

#	ARTICLE	IF	CITATIONS
1	6 kV/3.4 m ² Vertical $\text{In}^{2-}\text{Ga}^{2-}\text{O}^{3-}$ Schottky Barrier Diode With $\text{BV}^2/\text{Ron,sp}$ Performance Exceeding 1-D Unipolar Limit of GaN and SiC. IEEE Electron Device Letters, 2022, 43, 765-768.	3.9	65
2	Low density of interface trap states and temperature dependence study of Ga ₂ O ₃ Schottky barrier diode with p-NiOx termination. Applied Physics Letters, 2022, 120, .	3.3	38
3	$\text{In}^{2-}\text{Ga}_2\text{O}_3$ hetero-junction barrier Schottky diode with reverse leakage current modulation and $\text{BV}^2/\text{Ron,sp}$ value of 0.93 GW/cm ² . Applied Physics Letters, 2021, 118, .	3.3	72
4	Impact of Implanted Edge Termination on Vertical $\text{In}^{2-}\text{Ga}^{2-}\text{O}^{3-}$ Schottky Barrier Diodes Under OFF-State Stressing. IEEE Transactions on Electron Devices, 2020, 67, 3948-3953.	3.0	26
5	Lateral $\text{In}^{2-}\text{Ga}^{2-}\text{O}^{3-}$ MOSFETs With High Power Figure of Merit of 277 MW/cm ² . IEEE Electron Device Letters, 2020, 41, 537-540.	3.9	89
6	High-Performance Vertical $\text{In}^{2-}\text{Ga}^{2-}\text{O}^{3-}$ Schottky Barrier Diode With Implanted Edge Termination. IEEE Electron Device Letters, 2019, 40, 1788-1791.	3.9	84